

[PIXEL STRUCTURE AND FABRICATING METHOD THEREOF]

Abstract

A method of fabricating a pixel structure. A gate is formed over the substrate and then an insulation layer is formed over the substrate covering the gate. A channel layer is formed over the insulation layer above the gate. A pair of source/drain terminals is formed over the channel layer, thereby producing a thin film transistor on the substrate. A passivation layer is formed over the substrate covering the thin film transistor. A photoresist layer is formed over the passivation layer. Using the gate, the source/drain terminals as a mask, a back exposure process and a photoresist development are sequentially conducted to pattern the photoresist layer. Using the patterned photoresist layer as an etching mask, the passivation layer and the insulation layer are etched to expose a sidewall of the drain terminal. The photoresist layer is removed. A pixel electrode is formed over the passivation layer such that the pixel electrode and the drain terminal are electrically connected through the sidewall of the drain terminal.